Stacking of oligo and polythiophenes cations in solution: surface tension and dielectric saturation

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Abstract

The stacking of positively charged (or doped) terthiophene oligom ers and quaterthiophene polym ers in solution is investigated applying a recently developed uni ed electrostatic and cavitation m odel for rst-principles calculations in a continuum solvent. The therm odynam ic and structural patterns of the dimerization are explored in dimeration solvents, and the distinctive roles of polarity and surface tension are characterized and analyzed. Interestingly, we discover a saturation in the stabilization e ect of the dielectric screening that takes place at rather sm all values of $_0$. Moreover, we address the interactions in trimers of terthiophene cations, with the aim of generalizing the results obtained for the dimers to the case of higher-order stacks and nanoaggregates.

I. IN TRODUCTION

The interm olecular interactions between conjugated polymers and oligomers in the condensed phase whether in the solid state or in solution entails a fundamental interest in the emerging eld of molecular electronics, as they are decisive factors in the electronic and structural properties of these materials. The orientation and alignment of polymers in a solid matrix, the formation of aggregates in $\ln s$ and solution, or the ability of organic semiconductors to self-assemble are the outcome of a complex balance between the spatial features of the molecules and the substrate, and the interactions between them at the conditions of synthesis.¹ ⁶ By dictating rules for aggregation, these interactions eventually shape properties such as charge delocalization and mobility^{2,6} ⁸ or optical^{3,9} ¹¹ and electrom echanical¹² response.

Thiophene-derived oligon ers and polymers represent today one of the most promising class of organic sem iconductors, nding potential applications in a variety of electronic and electroactive devices.¹³ ¹⁵ Sem iconducting properties arise with doping, therefore much of the basic research performed on these systems has addressed in particular the doped or oxidized species. Since the early nineties electrochemical and spectroscopic evidence was gathered indicating that oxidized oligothiophenes reversibly associate in solution.¹⁶ ¹⁸ In a recent study,¹⁹ we have outlined how this association is driven by three contributions: the attractive – interactions, the Coulombic repulsion, and the solvent e ects. In the case of oligothiophene cations dimers, combination of sem iccoupied HOMOs form occupied bonding and empty antibonding orbitals, resulting in an interaction of covalent character, di erent in nature to the one arising in neutral dimers, of dispersive origin.²⁰ In vacuum, the electrostatic repulsion between the cations largely exceeds the covalent term,^{19,21} m aking

apparent the importance of the solvent (or of the counterions in the solid state case) in stabilizing the stacks. A polarizable dielectric medium favors concentration of charge in a small cavity, reverting the balance from net repulsion to attraction and stacking.

In the present paper, we employ a recently developed rst-principles approach recently developed to describe the e ect of a continuum solvent within the density-functional theory fram ework,²² and use it to explore the role of polarity and surface tension in the stabilization of dimers of polythiophene and oligothiophene radical cations. Furtherm ore, we exam ine the possibility of trim er form ation as an intermediate step toward the nucleation of higher-order aggregates, and to gain insight on self-assem bly in solution. In charged dimers, at variance with the case of neutral dimers governed by van-der-W aals forces, interactions are predominantly covalent and electrostatic, and density-functional theory (DFT) has proven to be su ciently accurate when compared with highly-correlated quantum -chemistry methods.¹⁹ In our approach, the contribution of the surface tension to the solvation free energy is computed in a very natural fashion, as the product between the area of the cavity and the surface tension of the solvation of the solvation is particularly in portant in dimerization processes, where the merging of two cavities into one provides an additional stabilizing term associated to the minimization of the total area of the cavity.

II. METHODOLOGY

All calculations in this work have been performed with the public domain CarParrinello parallel code included in the Quantum -ESPRESSO package,²³ based on density-functional theory, periodic-boundary conditions, and plane-wave basis sets. Vanderbilt ultrasoft pseudopotentials²⁴ have been used to represent the ion-electron interactions, in combination with the PBE approximation to the exchange-correlation term,²⁵ and with Kohn-Sham

orbitals and charge density expanded in plane waves up to a kinetic energy cuto of 25 and 200 Ry respectively.

Solvation is described with a continuum model recently implemented by us in the Quantum -ESPRESSO package and described in detail in reference 22 . In this approach, the solvent is represented as a dielectric medium surrounding a quantum -mechanical solute con ned in a cavity delimited by an isosurface of electronic charge density. Adopting a common decomposition of the solvation free energy G_{sol} we have:

$$G_{sol} = G_{el} + G_{cav} + G_{dis rep}$$
(1)

where G_{el} , G_{cav} , and $G_{dis rep}$ are the electrostatic, the cavitation, and the dispersionrepulsion contributions respectively.²⁶ In our implementation G_{el} and G_{cav} are considered explicitly, while $G_{dis rep}$ is largely captured (by virtue of the parametrization) by the electrostatic term. In the following, we brie y review the approaches used to obtain G_{el} and G_{cav} .

The electrostatic interaction between the dielectric medium and the solute is calculated, as proposed by Fattebert and $G ygi^{27,28}$ by solving the Poisson equation in the presence of a dielectric continuum with permittivity []:

$$r$$
 ([] r) = 4 : (2)

The function [] is de ned to asymptotically approach the permittivity of the bulk solvent $_{0}$ in regions of space where the electron density is low, and to approach 1 in those regions where it is high.²² In this way the dielectric medium and the electronic density respond self-consistently to each other through the dependence of on and vice-versa. The variation in the dielectric constant at the solvent-solute interface is controlled by two parameters $_{0}$ and , which determ ine the size of the cavity and the sm oothness of the transition region.

These are the only parameters entering the model, and our chosen values, $_0 = 0.00078$ e and = 1.3, represent a rather universal choice.²²

The cavitation term is computed as the product between the surface tension of the solvent and the area of the cavity,

$$G_{cav} = S(_{0}); \qquad (3)$$

where S (₀) is the surface of the same cavity employed in the electrostatic part of the solvation energy and is de ned by an isosurface of the charge density. This area can be easily and accurately calculated by integration in a real-space grid, as the volum e of a thin lm delimited between two charge density isosurfaces, divided by the thickness of this lm. This idea has been originally proposed by Cococcioniet al.²⁹ to de ne a \quantum surface" in the context of extended electronic-enthalpy functionals:

$$S(_{0}) = {}^{Z} dr {}^{n} \#_{_{0} \frac{1}{2}} [(r)] \#_{_{0} \frac{1}{2}} [(r)] {}^{o} \frac{jr (r)j}{1};$$
(4)

The nite-di erences parameter determines the separation between two adjacent isosurfaces, one external and one internal, corresponding to density thresholds $_0$ =2 and $_0$ + =2 respectively. The spatial distance between these two cavities or the thickness of the lm | is given at any point in space by the ratio =jr j. The (sm oothed) step function # is zero in regions of low electron density and approaches 1 otherwise, and it has been de ned consistently with the dielectric function [].

III. RESULTS AND DISCUSSION

C rystallographic data³⁰ and recent calculations^{19,21} on oxidized dimers have indicated that the stacking of oligothiophene cations follows a \slipped" pattern where the layers are shifted along the molecular axis, as shown in Fig.1.W e have studied the dependence of the

energy as a function of the lateral shift for oxidized terthiophene and polyquaterthiophene dimension acetonitrile ($_0 = 35.7$ and = 28.7 m N/m) at a xed intradimer separation of 3.4 A. In the calculations involving the terthiophene oligom ers, D irichlet boundary conditions in the electrostatic potential were applied, and the size of the unit cell was large enough to eliminate any signi cant interactions between the periodic images. In the case of the polymers, periodic boundary conditions were used along the z axis (the molecular axis), keeping the D irichlet boundary conditions in the other directions. The total charge of these system s is +2 (in the polymer, there is a positive charge every four thiophene rings). Our results are shown in Fig. 2: both the oligom er and the polym er exhibit a sim ilar pattern, with a globalm inimum at 2.3 A for the terthiophene and 2.0 A for the polyquaterthiophene. A local minimum at 0.0 A (where the two layers are overlapping) is present in both cases. Interestingly, the net binding is very sensitive to the lateral shift, varying steeply in a range of 10 kcal/m ol as one layer is slipped over the other. At shifts of about 1 A o the m inim a, the - interaction between the cations appears clearly weakened, resulting in an unbound dim er.

The nature of the solvent doesn't have any signi cant e ect on this characteristic pattern, even if it a ects the magnitude of the interaction. This is shown in Fig. 3, where the terthiophene curve is displayed for three di erent media: acetonitrile, dichlorom ethane $(_0=8.9, =27.2 \text{ mN/m})$ and water $(_0=78.8, =72.2 \text{ mN/m})$. (We have chosen water as a case study given its distinctive polarity and surface tension, despite the low solubility exhibited by thiophene derivatives in this solvent.) Fig. 4 explicitly illustrates the role of the solvent in the binding of the terthiophene cations, by showing the interaction energy as a function of the intradim er distance at a xed lateral shift of 2.3A. The binding energies are close to 5 kcal/m ol for dichlorom ethane and acetonitrile, and 12 kcal/m ol in water. These

energies can be seen as a lower lim it for the absolute value of the dimerization enthalpy H_d, since the e ect of the ionic environment was neglected in the calculations (the counterions in solution would di erentially stabilize the doubly-charged terthiophene dimer compared to two terthiophene cations. This e ect has been recently discussed by Jakow ski and $Sim on s^{31}$ for dimers of tetracyanoethylene anions, $[ICNE]_2^2$). In fact, dimerization enthalpies between 7 and 14 kcal/m olhave been reported for di erent terthiophene derivatives in apolar solvents.^{32 34} The interplanar separations corresponding to the minima, in the range of 3.4 to 3.5 A, are consistent with the distance of 3.47 A obtained for substituted terthiophene cations in the solid state.³⁰ Fig. 5 compares the potential energy surface of the oligom er with the one corresponding to the polymer (the later was calculated at a xed lateral shift of 2.0 A). The equilibrium distance turns out around 0.3 A larger in the periodic system, although it exhibits a slightly stronger binding. This is in agreem ent with experim ental data showing that H_d is enhanced by the length of the chain I^{17} a trend related to a \dilution" of the Coulom bic repulsion as the ratio between charge and oligom er size decreases.¹⁹ At the same time, however, the increase in length at a given oxidation state would diminish the ratio between unpaired electrons available to - bonding and thiophene rings, what would presum ably revert the aforem entioned binding trend starting from certain molecular weighs.35

The separate roles played by the dielectric screening of the solvent and its surface tension in the stabilization of the dimer are highlighted in Fig. 6. If the contribution of G_{cav} were om itted, the binding curves would turn out to be very close to each other (Fig. 6a). The larger in the case of water (72.2 m N/m versus 28.7 m N/m in acetonitrile) is responsible for the deeperm inimum in the potential energy surface. The net e ect of the surface tension is to m inimize the area of the solvation cage, monitored in Fig. 6b as the cations are pulled

apart. Beyond a separation of about 4.75 A the surface rem ains constant, indicating that the single cavity has split and each cation is enclosed in a separate cavity of area independent of the interplanar distance. In this situation there is no cavitation energy gain and therefore the curves excluding and including G_{cav} (open and closed symbols in Fig. 6a respectively) overlap on the right part of the plot.

The potential energy curves in Fig. 6a unveil an intriguing possibility: that the binding energy is not directly related to the dielectric constant of the solvent, as our intuition m ay suggest. This hypothesis is explored in Fig. 7, where the interaction energy between two terthiophene cations separated by 3.6 A is plotted as a function of the dielectric constant, ignoring the contribution of the surface tension. The results are somehow unexpected: a rather sm all increase in the permittivity with respect to the vacuum limit rapidly stabilizes the dimer, but once the dielectric constant is above 10 the e ect of a further increase in polarity is very small. This behavior can be rationalized considering that a polarizable dielectric medium with low permittivity is already enough to screen most of the Coulombic repulsion between the two charges and to favor aggregation of these charges by polarizing itælf. We note in passing that the positive drift obærved at higher permittivities for the case of $_0 = 0.00078$ e is an artifact of the continuum m odel. Since the dielectric constant is de ned as a continuous function of the electron density, its value throughout the intradim er region may depart from 1, allowing the dielectric medium to 11 some of the space between the cations and to interfere, though modestly, with the - bond. This e ect will be enhanced at large values of $_0$ and $_0$. In reality, instead, the solvent does not penetrate the intradim er space if the separation is 3.6 A, regardless of $_0$. This spurious behavior is in fact absent in the curve computed with $_0 = 0.0003$ in Fig. 7. W hat is remarkably captured by the continuum model is the saturation e ects of polarity on the dimerization, occurring already

for very low dielectric constants. These results are pretty much consistent with experimental observations that turn down a direct correlation between dimerization trends and polarity of the medium, while emphasizing the dependence on solubility of the oligothiophenes.³⁶ To understand the elect of the solvent on H_d , then, one should consider other properties such as surface tension or species content on between the solute and the medium.

A re the therm odynam ic and structural features found so far for the dim erization applicable to the stacking of multiple oligom er layers? It would be very interesting to know if or how the present results can be extended to processes such as aggregation and self-assembly in solution, involving the collective pairing of many oligothicphene units. In an attempt to o er an answer, even if prelim inary, to this question, we have studied the form ation of trimers of terthiophene cations in acetonitrile. Fig. 8 depicts the two con gurations of minin um energy obtained for the trimer in acetonitrile, in which the third cation is shifted by + or -2.3 A with respect to the next oligom er. As shown in Fig. 9, where the interaction energy is plotted as a function of the lateral shift of the third cation, there is no signi cant energetic di erence between these two minima. The curve corresponding to the dimer is plotted in the same qure: the pattern of valleys and peaks is preserved at the same lateral displacements when increasing the number of layers from two to three. The di erences in the relative depths of these curves can be ascribed to the fact that the same interplanar separation of 3.4 A was adopted in the calculation of both, but the optim al separation in the trimer is longer, as can be seen in Fig. 10. This graph shows the interaction energy calculated for the trimer in acetonitrile as a function of the interplanar separation between layers (the interplanar separation between the st and the second layer is the same as between the second and the third at each point of the curve). For meaningful comparison with the dimer, depicted in the same graph, the energies were normalized to the number

of -pairs, in this case two. Interestingly, the binding between two cations doesn't seem to be in paired by the presence of a third one: the interaction between stacks remains almost constant, even though the equilibrium distance increases in about 0.1 A. This suggests that the energetic and structural results found for the cation dimers can be applied, to a large extent, to the case of more complex, larger aggregates consisting of multiple layers.

IV. SUMMARY

Our study has highlighted the separate roles of surface tension the dielectric screening in the stabilization of charged thiophene oligom ers and polym ers stacks. The surface tension of the solvent is a driving force toward the minimization of the cavity area, and therefore toward dimerization: there is an energetic payo in accommodating two solutes in a single cavity of an area smaller than twice the one corresponding to the dissociated components. On the other hand, the dependence of the dimer stability on the polarity of the solvent alone is less evident. A dielectric elect is necessary to screen the electrostatic repulsion and to stabilize the charges in a small volume, but once the permittivity has reached a certain threshold, a further increase in polarity has a negligible contribution to the stabilization of the system. This observation is probably general to any -dimer of charged radicals an hypothesis that could be interesting to test through explicit calculation.

The form ation of trim ers follows the same geom etrical arrangement as the dimerization. A -bond on one of the oligomer planes does not seem to significantly a left the bond on the other. These results point to the conclusion that the organization of aggregates and stacks is governed by the same therm odynamics that is already manifest in the dimerization.

V. ACKNOW LEDGMENTS

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Figure Captions:

Figure 1.: A terthiophene dimer in the minimum energy con guration corresponding to the doubly-charged state, in which one singly-charged monomer is shifted 2.3 A with respect to the other along the main axis.

F igure 2.: Interaction energy as a function of the axial shift for the oxidized terthiophene and quaterthiophene dimers in acetonitrile.

Figure 3.: Interaction energy as a function of the axial shift for the oxidized terthiophene dimer in water ($_0 = 78.8$, = 72.2 m N/m), acetonitrile ($_0 = 35.7$, = 28.7 m N/m), and dichlorom ethane ($_0 = 8.9$, = 27.2 m N/m).

Figure 4.: Interaction energy as a function of the interplanar separation between two singly-charged terthiophene cations in water, acetonitrile, and dichlorom ethane.

Figure 5.: Interaction energy as a function of the interplanar separation for the doublycharged dimers of polyquaterthicphene (open symbols) and terthicphene (closed symbols) in dichlorom ethane and acetonitrile.

F igure 6.: (a) Interaction energy of two terthiophene cations in acetonitrile and in water, as a function of its separation. Open symbols curves were calculated om itting the cavitation contribution to the solvation energy, while the closed symbols curves include both the electrostatic and cavitation contributions. (b) A rea of the solvation cavity as a function of the separation between the terthiophene cations. Beyond 4.75 A the cavity splits in two, and the plotted area corresponds to two cavities containing one singly-charged terthiophene each.

Figure 7.: Interaction energy between two terthiophene cations at a xed separation as a function of the dielectric constant of the solvent, om itting the cavitation energy term, for

two di erent thresholds $_0$. The positive drift observed at high permittivity for $_0 = 0.00078$ e is an artifact of the continuum model (see text).

Figure 8.: Minimum energy structures for the terthiophene trimer in acetonitrile, surrounded by its corresponding solvation cavities de ned by isosurfaces at 0.00078e.

Figure 9.: Interaction energy as a function of the axial shift between a doubly-charged terthiophene dimer and a third terthiophene cation in acetonitrile.

Figure 10.: Interaction energy as a function of the interplanar separation between three parallel terthiophene cations in acetonitrile. The top and the bottom layers are overlapping with each other, having an axial shift of 2.3 A with respect to the central layer, as shown in Fig. 8a.

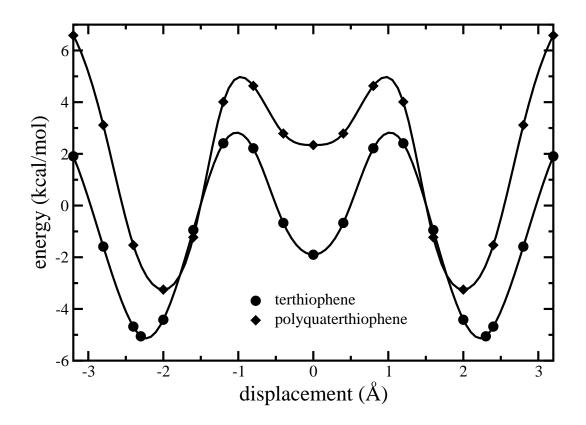


FIG.2:D.Scherlis

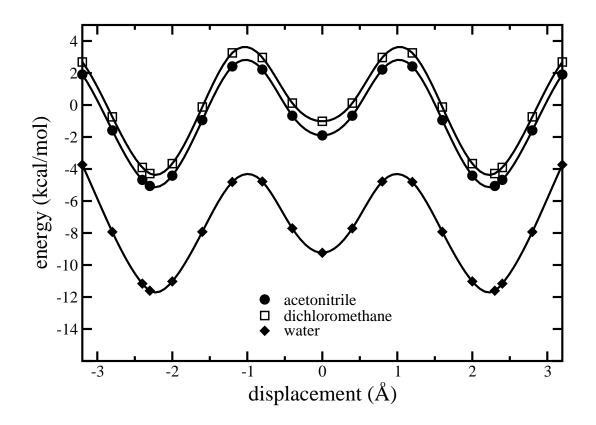


FIG.3:D.Scherlis

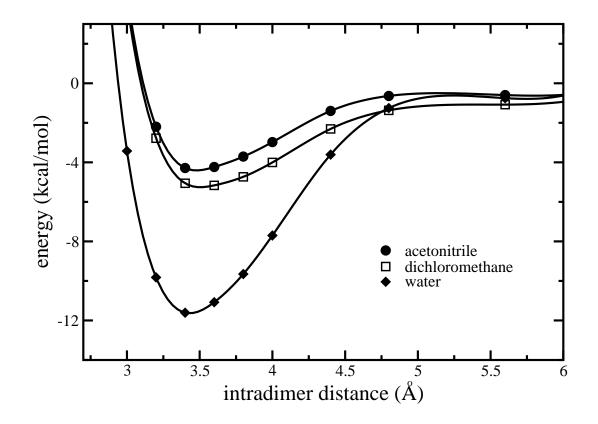


FIG.4:D.Scherlis

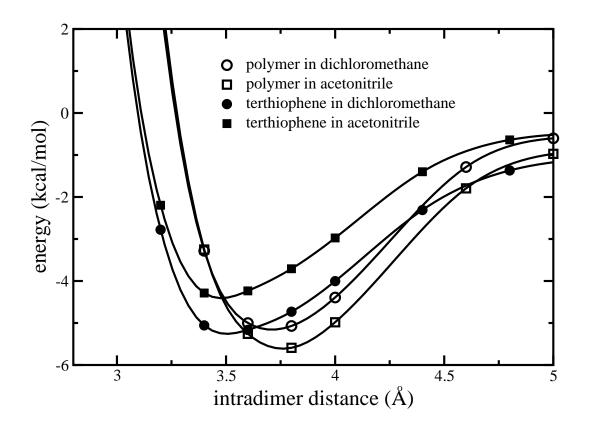


FIG.5:D.Scherlis

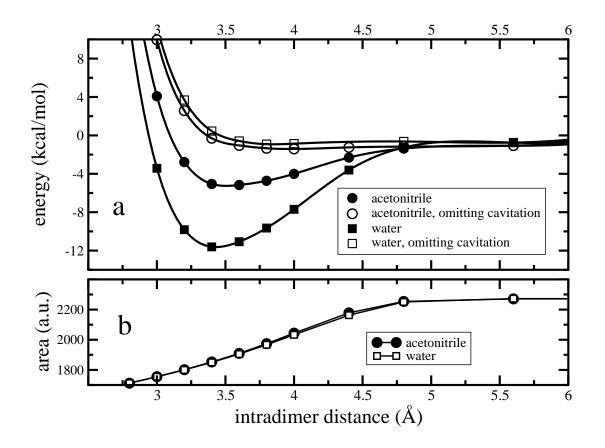


FIG.6:D.Scherlis

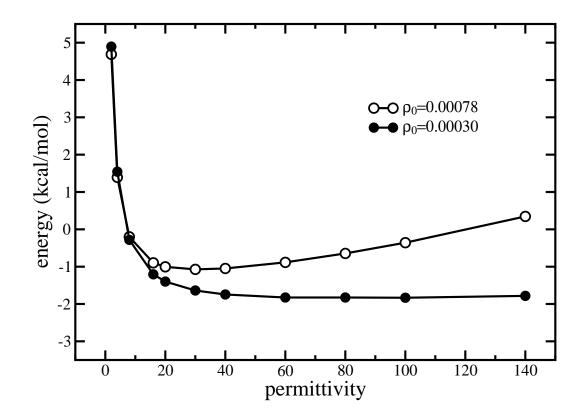


FIG.7:D.Scherlis

FIG.8:D.Scherlis

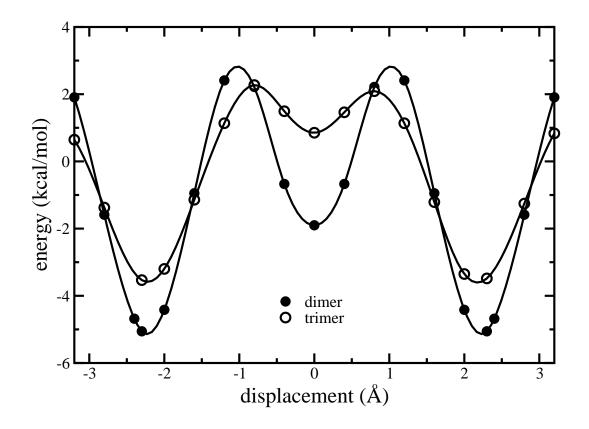


FIG.9:D.Scherlis

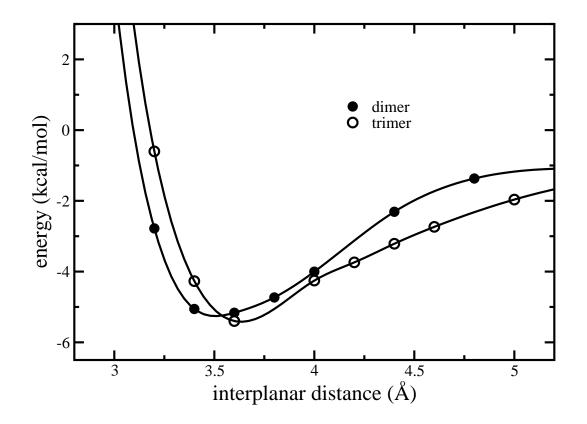


FIG.10:D.Scherlis

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